



SI7137DP-T1-GE3 Information



For Reference Only

Part Number SI7137DP-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 20V 60A PPAK SO-8

Package PowerPAK? SO-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI7137DP-T1-GE3 Specifications

Manufacturer Part NumberSI7137DP-T1-GE3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackagePowerPAK? SO-8SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)2.5V, 10VVgs(th) (Max) @ Id1.4V @ 250μAGate Charge (Qg) (Max) @ Vgs585nC @ 10VInput Capacitance (Ciss) (Max) @ Vds20000pF @ 10VVgs (Max)±12VFET Feature-Power Dissipation (Max)6.25W (Ta), 104W (Tc)Rds On (Max) @ Id, Vgs1.95 mOhm @ 25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8		
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Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Rds On (Max) @ Id, Vgs	1.95 mOhm @ 25A, 10V
Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case PowerPAK? SO-8	Mounting Type	Surface Mount
	Supplier Device Package	PowerPAK? SO-8
Report errors?	Package / Case	PowerPAK? SO-8
		Report errors?

SI7137DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7137DP-T1-GE3 Payment Methods



















SI7137DP-T1-GE3 Shipping Methods













If you have any question about SI7137DP-T1-GE3, please do not hesitate to contact us!

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